MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# SSM3K341TU

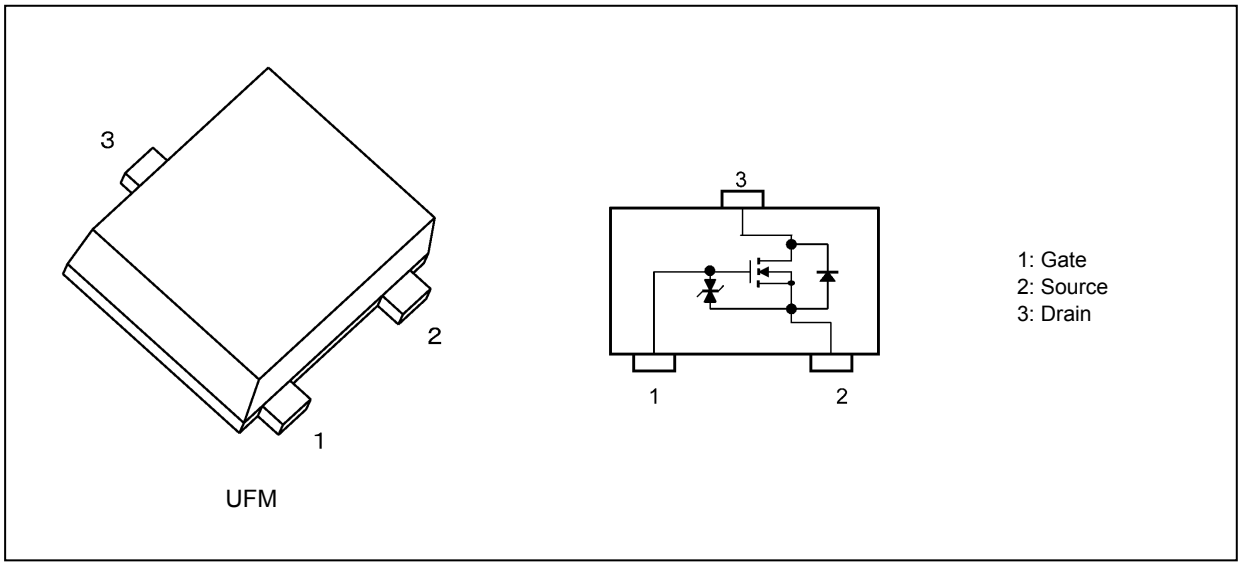
## 1. Applications

- Power Management Switches
- DC-DC Converters

## 2. Features

(1) AEC-Q101 qualified (Please see the orderable part number list)
(2) 175 ℃ MOSFET
(3) 4.0 V drive
(4) Low drain-source on-resistance
: $R_{DS(ON)}$ = 28 mΩ (typ.) (@$V_{GS}$ = 10 V)
$R_{DS(ON)}$ = 36 mΩ (typ.) (@$V_{GS}$ = 4.5 V)
$R_{DS(ON)}$ = 43 mΩ (typ.) (@$V_{GS}$ = 4 V)

## 3. Packaging and Internal Circuit




## 4. Orderable part number

| Orderable part number | AEC-Q101 | | Note | |
|---|---|---|---|---|
| SSM3K341TU,LF | — | | General Use | |
| SSM3K341TU,LXGF | YES | (Note 1) | Unintended Use | (Note 1) |
| SSM3K341TU,LXHF | YES | | Automotive Use | |

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production
2016-12

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## 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a$ = 25 °C)

| Characteristics | | | Symbol | Rating | Unit |
|---|---|---|---|---|---|
| Drain-source voltage | | | $V_{DSS}$ | 60 | V |
| Gate-source voltage | | | $V_{GSS}$ | ±20 | |
| Drain current (DC) | | (Note 1) | $I_D$ | 6 | A |
| Drain current (pulsed) | | (Note 1), (Note 2) | $I_{DP}$ | 24 | |
| Power dissipation | | (Note 3) | $P_D$ | 1.0 | W |
| Power dissipation | (t = 10 s) | (Note 3) | $P_D$ | 1.8 | |
| Single-pulse avalanche energy | | (Note 4) | $E_{AS}$ | 28.9 | mJ |
| Avalanche current | | | $I_{AR}$ | 6 | A |
| Channel temperature | | (Note 5) | $T_{ch}$ | 175 | °C |
| Storage temperature | | (Note 5) | $T_{stg}$ | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: pulse width ≤ 1 ms, Duty ≤ 1 %

Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 $mm^2$)

Note 4: $V_{DD}$ = 25 V, $T_{ch}$ = 25 °C (Initial state), L = 1 mH, $R_G$ = 25 Ω

Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, $P_D$, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

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# 6. Electrical Characteristics

## 6.1. Static Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|---|
| Gate leakage current | | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±16 V | — | — | ±10 | μA |
| Drain cut-off current | | $I_{DSS}$ | $V_{DS}$ = 60 V, $V_{GS}$ = 0 V | — | — | 1 | |
| Drain-source breakdown voltage | | $V_{(BR)DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 60 | — | — | V |
| Drain-source breakdown voltage | (Note 1) | $V_{(BR)DSX}$ | $I_D$ = 10 mA, $V_{GS}$ = -20 V | 40 | — | — | |
| Gate threshold voltage | (Note 2) | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 0.1 mA | 1.5 | — | 2.5 | |
| Drain-source on-resistance | (Note 3) | $R_{DS(ON)}$ | $I_D$ = 2 A, $V_{GS}$ = 4 V | — | 43 | 69 | mΩ |
| | | | $I_D$ = 3 A, $V_{GS}$ = 4.5 V | — | 36 | 51 | |
| | | | $I_D$ = 4 A, $V_{GS}$ = 10 V | — | 28 | 36 | |

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let $V_{th}$ be the voltage applied between gate and source that causes the drain current ($I_D$) to below (0.1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than $V_{th}$, and $V_{GS(OFF)}$ must be lower than $V_{th}$. This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.
Take this into consideration when using the device.

Note 3: Pulse measurement.

## 6.2. Dynamic Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz | — | 550 | — | pF |
| Reverse transfer capacitance | $C_{rss}$ | | — | 35 | — | |
| Output capacitance | $C_{oss}$ | | — | 300 | — | |
| Switching time (rise time) | $t_r$ | $V_{DD}$ = 30 V, $I_D$ = 3 A, $V_{GS}$ = 0 to 4.5 V, $R_G$ = 50 Ω Duty ≤ 1 %,Input: $t_r$, $t_f$ < 5 ns, Common source, See Chapter 6.3. | — | 48 | — | ns |
| Switching time (turn-on time) | $t_{on}$ | | — | 63 | — | |
| Switching time (fall time) | $t_f$ | | — | 6 | — | |
| Switching time (turn-off time) | $t_{off}$ | | — | 18 | — | |

## 6.3. Switching Time Test Circuit

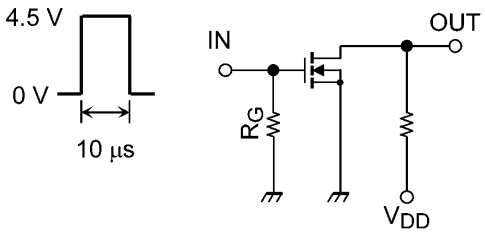



Fig. 6.3.1 Switching Time Test Circuit

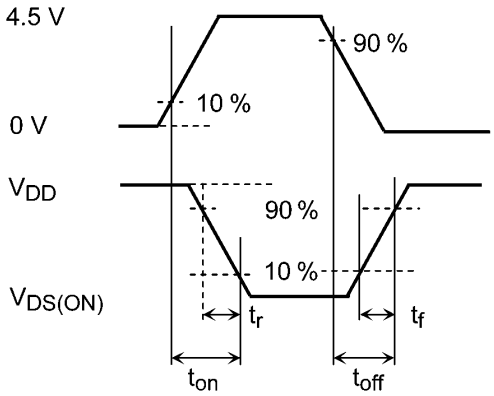



Fig. 6.3.2 Input Waveform/Output Waveform

## 6.4. Gate Charge Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Total gate charge (gate-source plus gate-drain) | $Q_g$ | $V_{DD}$ = 48 V, $I_D$ = 2 A, $V_{GS}$ = 10 V | — | 9.3 | — | nC |
| Gate-source charge 1 | $Q_{gs1}$ | | — | 1.8 | — | |
| Gate-drain charge | $Q_{gd}$ | | — | 2.0 | — | |

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### 6.5. Source-Drain Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Diode forward voltage (Note 1) | $V_{DSF}$ | $I_D$ = -6 A, $V_{GS}$ = 0 V | — | -0.9 | -1.5 | V |

Note 1: Pulse measurement.

## 7. Marking

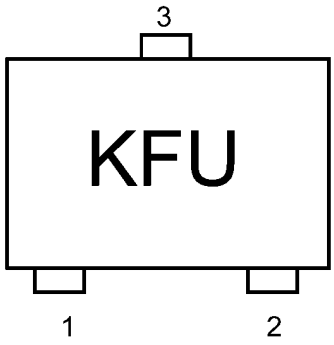



**Fig. 7.1 Marking**

## 8. Characteristics Curves (Note)

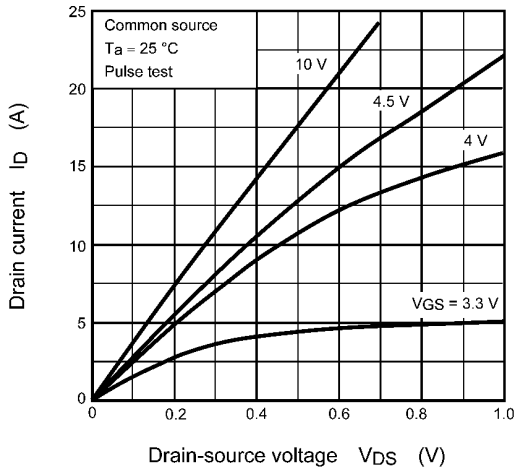



Fig. 8.1 $I_D$ - $V_{DS}$

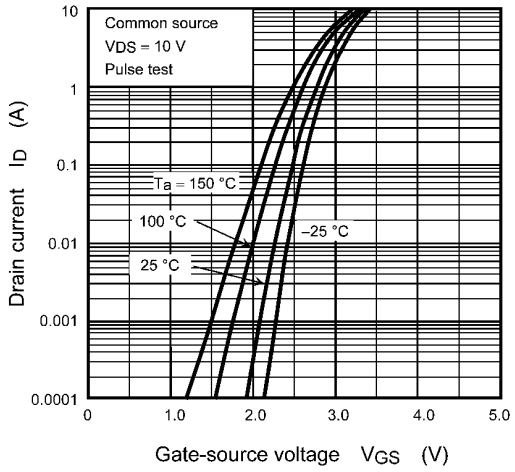



Fig. 8.2 $I_D$ - $V_{GS}$

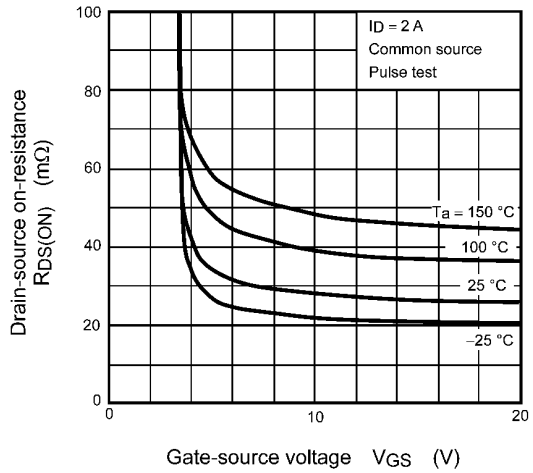



Fig. 8.3 $R_{DS(ON)}$ - $V_{GS}$

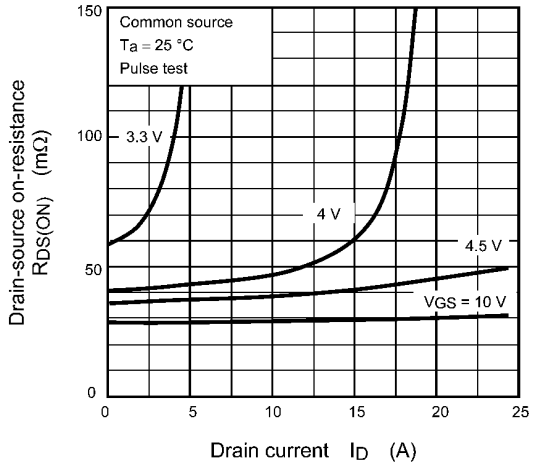



Fig. 8.4 $R_{DS(ON)}$ - $I_D$

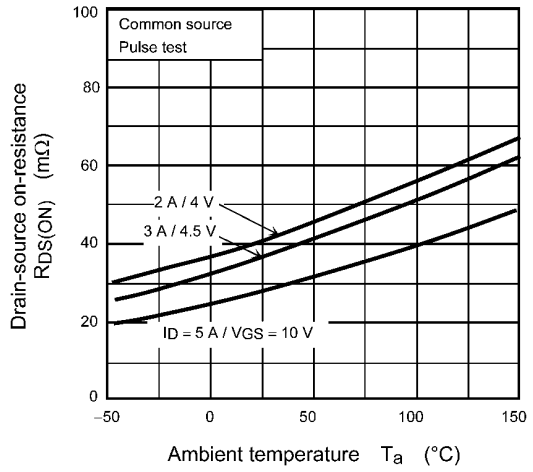



Fig. 8.5 $R_{DS(ON)}$ - $T_a$

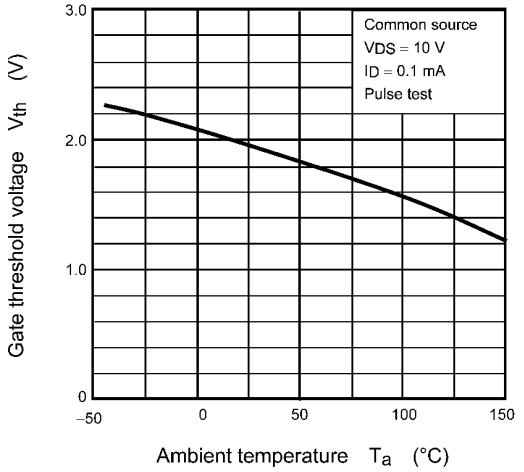



Fig. 8.6 $V_{th}$ - $T_a$

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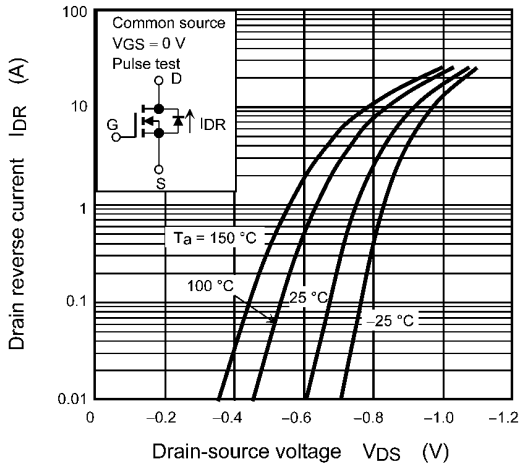



Fig. 8.7 $I_{DR}$ - $V_{DS}$

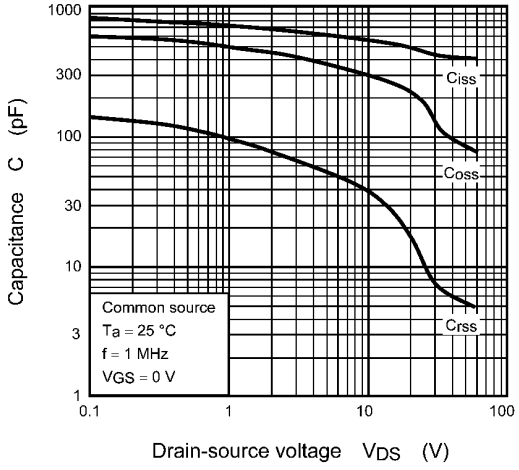



Fig. 8.8 C - $V_{DS}$

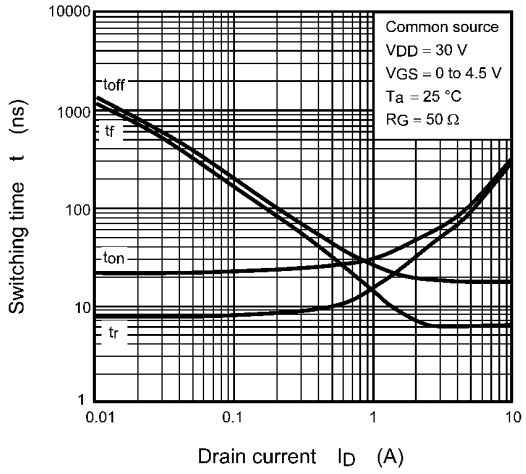



Fig. 8.9 t - $I_D$

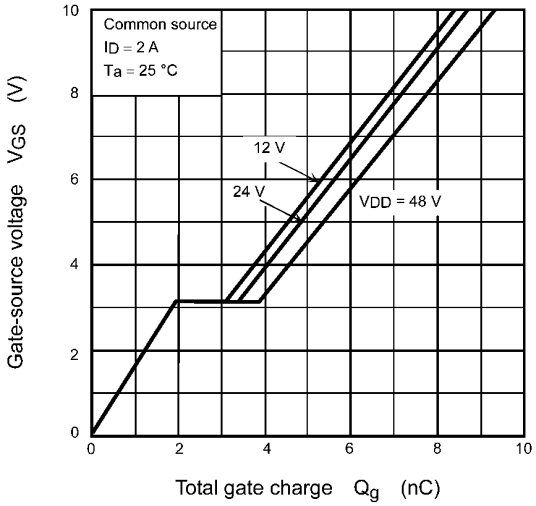



Fig. 8.10 Dynamic Input Characteristics

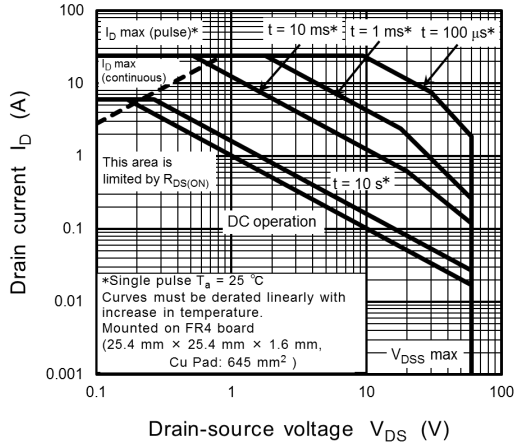



Fig. 8.11 Safe Operating Area

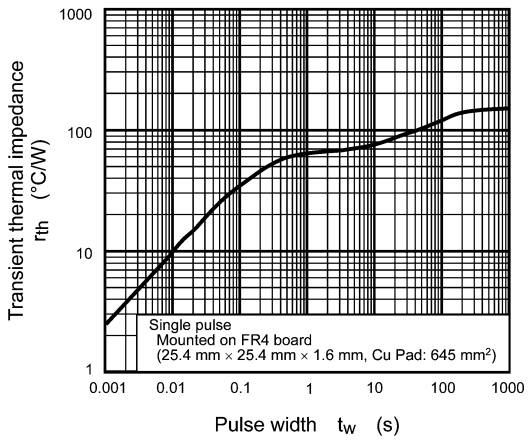


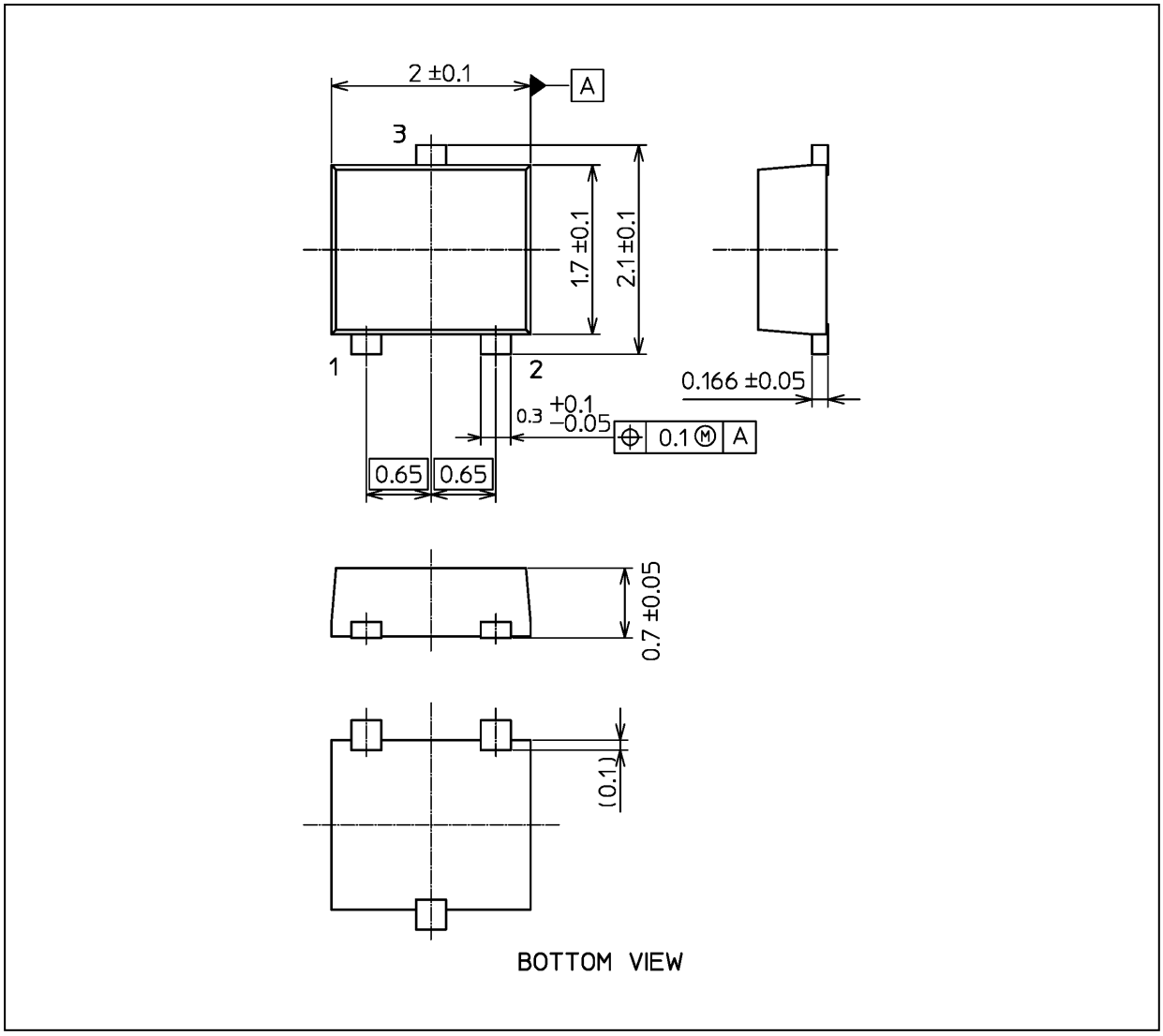

Fig. 8.12 $r_{th}$ - $t_w$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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## Package Dimensions

Unit: mm




Weight: 6.6 mg (typ.)

| Package Name(s) |
| --- |
| Nickname: UFM |

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